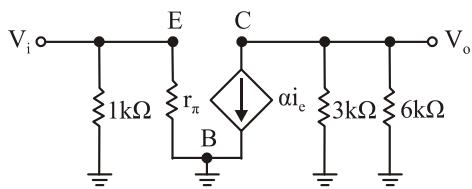






41.  $v_i = i_e \times r_e$ ,  $v_o = \beta \times i_b \times (3 k\Omega // 6 k\Omega)$

$$A_v = \frac{V_o}{V_i} = \frac{99 \times i_b \times 2 k\Omega}{100 \times i_b \times 50 \Omega} = 39.6$$



42. 達靈頓電路具有以下特性

- (A) 高輸入阻抗
- (B) 低輸出阻抗
- (C) 電壓增益近似於 1，但略小於 1
- (D) 高電流增益

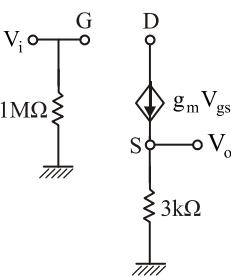
43. (B) 場效電晶體之放大倍數  $\mu$  通常比電晶體的順向電流轉換比  $\beta$  小，因此場效電晶體之增益通常比電晶體低

44. (D) 當  $|V_{DS}|$  很小時，JFET 位於歐姆區

45.  $V_o = g_m \times V_{gs} \times R_s$

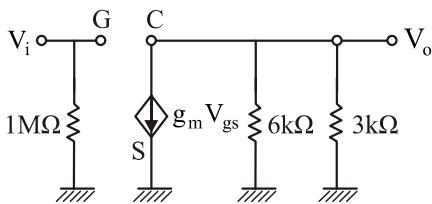
$$V_i = V_{gs} + g_m \times V_{gs} \times R_s$$

$$A_v = \frac{V_o}{V_i} = \frac{3 \frac{mV}{V} \times 3 k\Omega}{1 + 3 \frac{mV}{V} \times 3 k\Omega} = 0.9$$



46.  $V_i = V_{gs}$ ,  $V_o = -g_m \times V_{gs} \times (6 k\Omega // 3 k\Omega)$

$$A_v = \frac{V_o}{V_i} = -g_m \times (6 k\Omega // 3 k\Omega) = -5 \frac{mA}{V} \times 2 k\Omega = -10$$

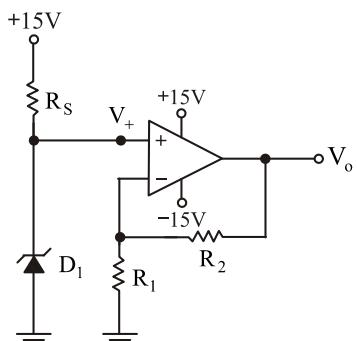


47. 題目為減法電路

$$V_o = \frac{R_3}{R_1} (V_2 - V_1) = \frac{2 k}{1 k} (3 V - 1 V) = 4 V$$

49.  $V_- = V_+ = V_Z = 3 V$ ,  $V_o = V_- \times (1 + \frac{R_2}{R_1})$

$$= 3 \times (1 + \frac{2 k\Omega}{1 k\Omega}) = 9 V$$



50. (1)  $V_{H^+} = V_{T^+} = V_{O^+(sat)} \times \frac{R_1}{R_1 + R_2} + V_{ref} \times \frac{R_2}{R_1 + R_2}$   
 $= 15 \times \frac{2 k}{2 k + 8 k} + 2 \times \frac{8 k}{2 k + 8 k} = 4.6 V$

(2)  $V_{H^-} = V_{T^-} = V_{O^-(sat)} \times \frac{R_1}{R_1 + R_2} + V_{ref} \times \frac{R_2}{R_1 + R_2}$   
 $= -15 \times \frac{2 k}{2 k + 8 k} + 2 \times \frac{8 k}{2 k + 8 k} = -1.4 V$

(3)  $V_H = V_{H^+} - V_{H^-} = 6 V$